



JST04F-600CW 4A TRIAC

Rev.A.1.1

The JST04F-600CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST04F-600CW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST04F-600CW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

| Parameter | Symbol | Value | Unit |
|--|--------------|---------|------------------------|
| Storage junction temperature range | T_{stg} | -40-150 | |
| Operating junction temperature range | T_j | -40-125 | |
| Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$) | V_{DRM} | 600 | V |
| Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$) | V_{RRM} | 600 | V |
| RMS on-state current ($T_c=97^\circ\text{C}$) | $I_{T(RMS)}$ | 4 | A |
| Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$) | I_{TSM} | 40 | A |
| Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$) | | 44 | |
| I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$) | I^2t | 8 | A^2s |
| Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$) | di/dt | 80 | $\text{A}/\mu\text{s}$ |
| Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$) | I_{GM} | 4 | A |
| Average gate power dissipation ($T_j=125^\circ\text{C}$) | $P_{G(AV)}$ | 0.5 | W |

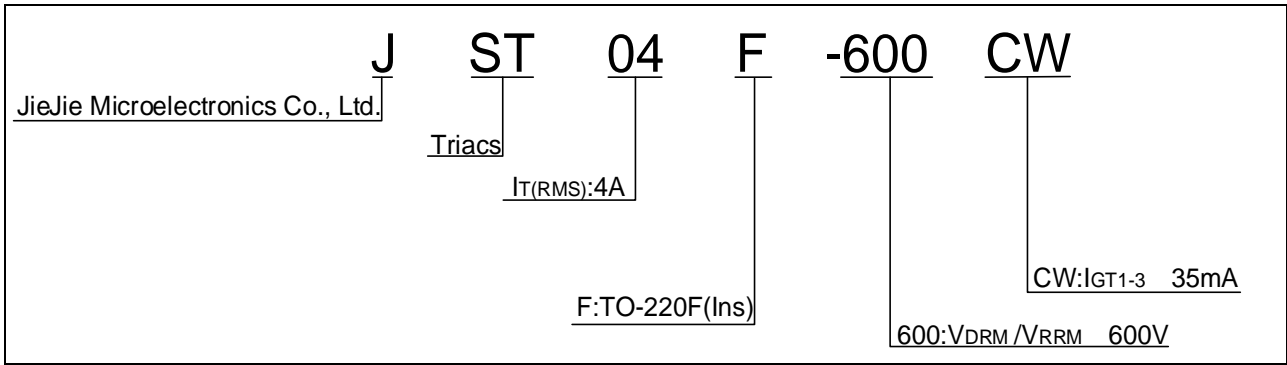
| | | | |
|--|----------|----|----|
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7) | V_{pp} | 4 | kV |

($T_j=25$ unless otherwise specified)

| Symbol | Test Condition | Quadrant | Value | | Unit |
|-----------|---|----------|-------|------|------------|
| I_{GT} | $V_D=12V R_L=33$ | - - | MAX. | 35 | mA |
| V_{GT} | | - - | MAX. | 1 | V |
| V_{GD} | $V_D=V_{DRM} T_j=125$ $R_L=3.3k$ | - - | MIN. | 0.2 | V |
| I_L | $I_G=1.2I_{GT}$ | - | MAX. | 50 | mA |
| | | | | 60 | |
| I_H | $I_T=100mA$ | | MAX. | 35 | mA |
| dV/dt | $V_D=400V$ Gate Open $T_j=125$ | | MIN. | 1500 | V/ μs |
| (dI/dt)c | (dV/dt)c=20V/ μs , $T_j=125$ | | MIN. | 8 | A/ms |
| t_{on} | $I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$ | | TYP. | 3 | μs |
| t_{off} | | | | 30 | |

| Symbol | Parameter | | Value(MAX.) | Unit |
|-----------|---------------------------|-----------|-------------|---------|
| V_{TM} | $I_{TM}=5A t_p=380\mu s$ | $T_j=25$ | 1.65 | V |
| V_{TO} | Threshold voltage | $T_j=125$ | 0.799 | V |
| R_D | Dynamic resistance | $T_j=125$ | 151 | m |
| I_{DRM} | $V_D=V_{DRM} V_R=V_{RRM}$ | $T_j=25$ | 5 | μA |
| I_{RRM} | | $T_j=125$ | 0.2 | mA |

| Symbol | Parameter | Value | Unit |
|---------------|--------------------------|-------|------|
| $R_{th(j-c)}$ | junction to case (AC) | 4.5 | /W |
| $R_{th(j-a)}$ | junction to ambient (AC) | 60 | /W |



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V V V

FIG.1: Maximum power dissipation versus RMS on-state current

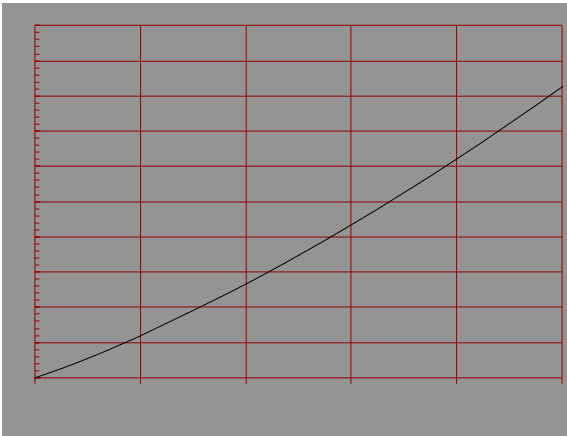


FIG.2: RMS on-state current versus case temperature

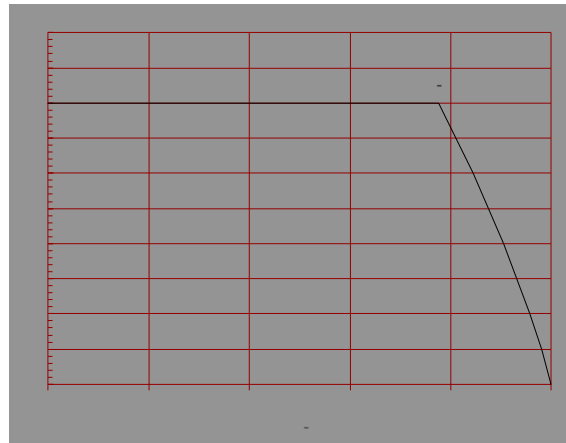


FIG.3: Surge peak on-state current versus number of cycles

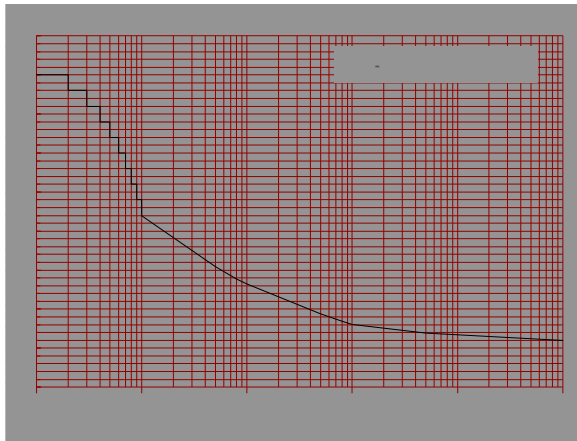
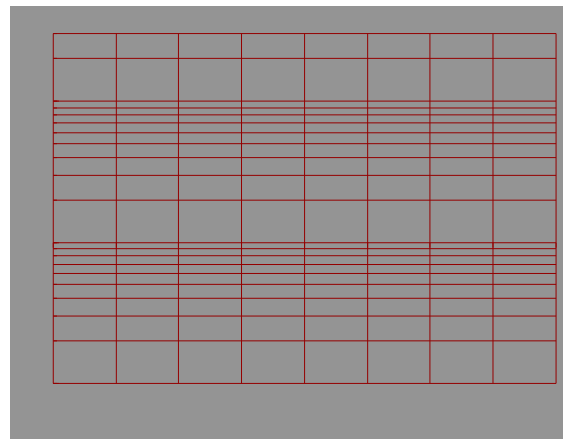


FIG.4: On-state characteristics





| Order code | Voltage V_{DRM}/V_{RRM} (V) | IGT(mA) | Package | Base qty. | Delivery mm |
|------------|----------------------------------|---------|---------|-----------|----------------|
|------------|----------------------------------|---------|---------|-----------|----------------|



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